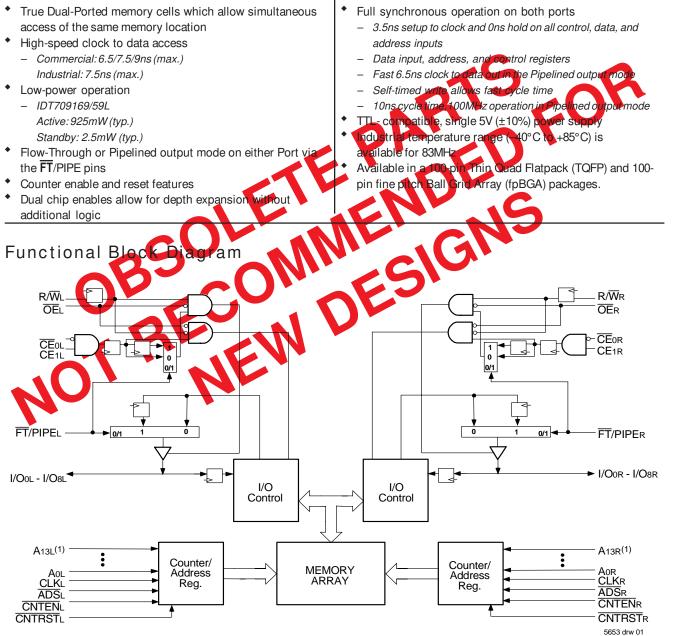


HIGH-SPEED 16/8K x 9 SYNCHRONOUS PIPELINED DUAL-PORT STATIC RAM

LEAD FINISH (SnPb) ARE IN EOL PROCESS - LAST TIME BUY EXPIRES JUNE 15, 2018

Features



NOTE:

1. A13 is a NC for IDT709159.

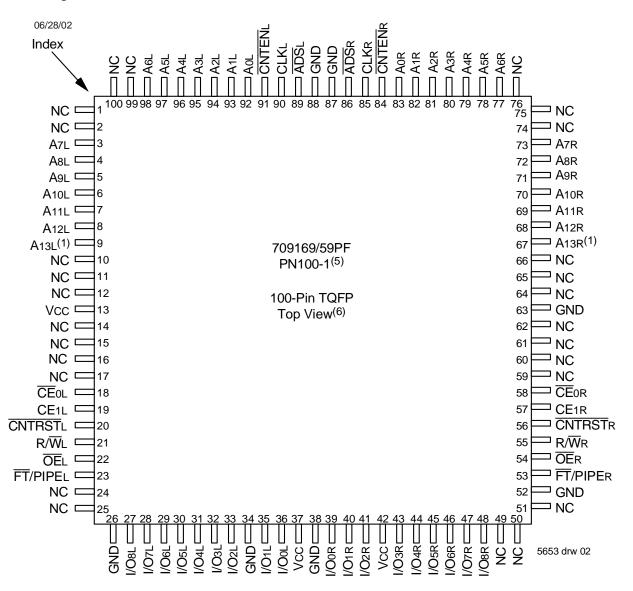


High-Speed 16/8K x 9 Synchronous Pipelined Dual-Port Static RAM

Description

The IDT709169/59 is a high-speed 16/8K x 9 bit synchronous Dual-Port RAM. The memory array utilizes Dual-Port memory cells to allow simultaneous access of any address from both ports. Registers on control, data, and address inputs provide minimal setup and hold times. The timing latitude provided by this approach allows systems to be designed with very short cycle times. With an input data register, the IDT709169/59 has been optimized for applications having unidirectional or bidirectional data flow in bursts. An automatic power down feature, controlled by \overline{CE}_0 and CE1, permits the on-chip circuitry of each port to enter a very low standby power mode. Fabricated using IDT's CMOS high-performance technology, these devices typically operate on only 925mW of power.

Pin Configurations^(1,2,3,4)



- 1. A13 is a NC for IDT709159.
- 2. All Vcc pins must be connected to power supply.
- 3. All GND pins must be connected to ground supply.
- 4. Package body is approximately 14mm x 14mm x 1.4mm.
- 5. This package code is used to reference the package diagram.
- 6. This text does not indicate orientation of the actual part-marking.

Pin Configurations $(con't.)^{(1,2,3,4)}$

06/28/02

709169/59BF BF100⁽⁵⁾

100-Pin fpBGA Top View⁽⁶⁾

00/20/02									
A1	a2	a3	A4	^{A5}	^{A6}	A7	^{A8}	^{A9}	A10
A6R	A9r	A12R	NC	GND	GND	NC	R/Wr	GND	NC
^{B1} A4R	b2 A5r	^{B3} A8R	B4 A10R	B5 NC	B6 NC	^{B7} NC	B8 OEr	^{B9} NC	b10 I/O6r
C1	C2	C3	C4	C5	C6		C8	C9	С10
A3R	NC	NC	A7R	NC	CE0R		PL/FTR	I/O7R	I/Озг
D1	D2	D3	D4	D5		D7	d8	d9	D10
Aor	CLKr	A1R	A2R	A11R		CNTRSTR	I/O8r	I/O5r	I/O1R
^{E1}	e2	E3	E4	e5	^{E6}	e7	e8	e9	E10
GND	ADSr	CNTEN _R	A1L	ADSl	GND	I/O4r	I/O2r	I/Oor	VCC
^{F1}	^{F2}	F3	F4	F5	^{F6}	F7	f8	f9	F10
GND	CLKL	Aol	A3L	VCC	GND	Vcc	I/O2l	I/O1l	I/Ool
G1	G2	G3	G4	G5	G6	^{G7} NC	g8	^{G9}	G10
CNTEN⊾	NC	A5L	A12L	NC	R∕₩L		I/O4l	GND	І/Озг
H1	H2	H3	H4	H5	H6	H7	h8	H9	h10
A2L	A4L	A9L	A13L ⁽¹⁾	NC	CE1L	NC	I/O7l	I/O6l	I/O5l
J1	J2	J3	J4	J5	J6	J7	_{J8}	^{J9}	J10
NC	A7L	A10L	NC	NC	NC	OEL	GND	GND	I/O8∟
K1 A6L	K2 A8L	K3 A11L	K4 NC	к5 Vcc	к ₆ Vcc		K8 CNTRST∟		к10 NC

5653 drw 03

NOTES:

1. A13 is a NC for IDT709159.

2. All Vcc pins must be connected to power supply.

3. All GND pins must be connected to ground supply.

4. Package body is approximately 10mm x 10mm x 1.4mm with 0.8mm ball pitch.

5. This package code is used to reference the package diagram.

6. This text does not indicate orientation of the actual part-marking.

High-Speed 16/8K x 9 Synchronous Pipelined Dual-Port Static RAM

Industrial and Commercial Temperature Ranges

Pin Names

Left Port	Right Port	Names
CEOL, CEIL	\overline{CE} OR, CE1R	Chip Enables
R/WL	R/₩R	Read/Write Enable
ŌĒL	ŌĒr	Output Enable
Aol - A13L ⁽¹⁾	Aor - A13r ⁽¹⁾	Address
I/O0L - I/O8L	I/O0r - I/O8r	Data Input/Output
CLKL	CLKR	Clock
<u>ADS</u> ∟	ADSR	Address Strobe
<u>CNTEN</u> L		Counter Enable
CNTRST ∟		Counter Reset
FT /PIPE∟	FT /PIPER	Flow-Through/Pipeline
V	сс	Power (5V)
G	ND	Ground (0V)

5653 tbl 01

NOTE:

1. A13 is a NC for IDT709159.

Truth Table I—Read/Write and Enable Control^(1,2,3)

ŌĒ	CLK	CE ₀	CE1	R∕₩	I/O0-8	Mode
х	\uparrow	Н	х	х	High-Z	Deselected—Power Down
х	\uparrow	х	L	х	High-Z	Deselected—Power Down
х	\uparrow	L	Н	L	DATAℕ	Write
L	\uparrow	L	н	Н	DATAOUT	Read
Н	х	L	Н	х	High-Z	Outputs Disabled

NOTES:

5653 tbl 02

1. "H" = VIH, "L" = VIL, "X" = Don't Care. 2. \overline{ADS} , \overline{CNTEN} , \overline{CNTRST} = X.

3. \overline{OE} is an asynchronous input signal.

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High-Speed 16/8K x 9 Synchronous Pipelined Dual-Port Static BA

Industrial and Commercial Temperature Ranges

Truth Table II—Address Counter Control^(1,2)

External Address	Previous Internal Address	Internal Address Used	CLK	ADS	CNTEN	CNTRST	I/O ⁽³⁾	MODE
An	х	An	Ŷ	L ⁽⁴⁾	Х	н	Dvo (n)	External Address Used
х	An	An + 1	Ŷ	Н	L ⁽⁵⁾	Н	D⊮o(n+1)	Counter Enabled—Internal Address generation
х	An + 1	An + 1	Ŷ	н	Н	Н	D⊮o(n+1)	External Address Blocked—Counter disabled (An + 1 reused)
х	х	A0	Ŷ	х	Х	L ⁽⁴⁾	Dvo(0)	Counter Reset to Address 0

NOTES:

 $1. \quad "H" = V{\scriptstyle IH}, "L" = V{\scriptstyle IL}, "X" = Don't \ Care.$

2. \overline{CE}_0 and \overline{OE} = VIL; CE1 and R/ \overline{W} = VIH.

3. Outputs configured in Flow-Through Output mode: if outputs are in Pipelined mode the data out will be delayed by one cycle.

4. $\overline{\text{ADS}}$ and $\overline{\text{CNTRST}}$ are independent of all other signals including $\overline{\text{CE}}_0$ and CE1.

5. The address counter advances if $\overline{\text{CNTEN}} = \text{VL}$ on the rising edge of CLK, regardless of all other signals including $\overline{\text{CE}}_0$ and CE1.

Recommended Operating Temperature and Supply Voltage

Grade	Ambient Temperature ⁽¹⁾	GND	Vcc
Commercial	0°C to +70°C	0V	5.0V <u>+</u> 10%
Industrial	-40°C to +85°C		5.0V <u>+</u> 10%

NOTES:

1. This is the parameter TA. This is the "instant on" case temperature.

Recommended DC Operating Conditions

Symbol	Parameter	Min.	Тур.	Max.	Unit
Vcc	Supply Voltage	4.5	5.0	5.5	V
GND	Ground	0	0	0	V
Vih	Input High Voltage	2.2	_	6.0 ⁽¹⁾	V
VIL	Input Low Voltage	-0.5 ⁽²⁾		0.8	V

NOTES:

5653 tbl 04

VTERM must not exceed Vcc + 10%.

2. VIL \geq -1.5V for pulse width less than 10ns.

Absolute Maximum Ratings⁽¹⁾ Symbol Rating Commercial Unit & Industrial VTERM⁽²⁾ Terminal Voltage -0.5 to +7.0 ٧ with Respect to GND TBIAS Temperature -55 to +125 °C Under Bias Tstg Storage -65 to +150 °C Temperature ЮUT DC Output 50 mΑ Current 5653 tbl 06

NOTES:

- Stresses greater than those listed under ABSOLUTE MAXIMUM RATINGS may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability.
- 2. VTERM must not exceed Vcc + 10% for more than 25% of the cycle time or 10ns maximum, and is limited to \leq 20mA for the period of VTERM \geq Vcc + 10%.

Capacitance⁽¹⁾ (TA = +25°C, f = 1.0MHz)

Symbo	Parameter	Conditions ⁽²⁾	Max.	Unit
Ciℕ	Input Capacitance	VIN = 3dV	9	pF
Cout ⁽³	Output Capacitance	Vout = 3dV	10	pF

NOTES:

1. These parameters are determined by device characterization, but are not production tested.

2. 3dV references the interpolated capacitance when the input and output switch from 0V to 3V or from 3V to 0V.

3. COUT also references CI/O.

5653 tbl 07

5653 tbl 05

5653 tbl 03

High-Speed 16/8K x 9 Synchronous Pipelined Dual-Port Static R

Industrial and Commercial Temperature Range

DC Electrical Characteristics Over the Operating Temperature Supply Voltage Range (Vcc = 5.0V ± 10%)

			70916		
Symbol	Parameter	Test Conditions	Min.	Max.	Unit
Lu	Input Leakage Current ⁽¹⁾	Vcc = 5.5V, VIN = 0V to Vcc	_	5	μA
llo	Output Leakage Current	\overline{CE}_0 = VIH or CE1 = VIL, VOUT = 0V to VCC	_	5	μA
Vol	Output Low Voltage	lol = +4mA	-	0.4	V
Vон	Output High Voltage	Юн = -4mA	2.4	-	v

NOTE:

1. At $Vcc \le 2.0V$ input leakages are undefined.

5653 tbl 08

DC Electrical Characteristics Over the Operating Temperature and Supply Voltage Range⁽³⁾ ($Vcc = 5V \pm 10\%$)

				<u> </u>			,				
						9/59L6 Only	709169 Com'l		709169 Com'l		
Symbol	Parameter	Test Condition	Versi	on	Typ. ⁽⁴⁾	Max.	Typ. ⁽⁴⁾	Max.	Typ. ⁽⁴⁾	Max.	Unit
ICC	Dynamic Operating Current	CEL and CER= VL	COM'L	L	230	430	210	400	185	360	mA
	(Both Ports Active)	Outputs Disabled $f = fMAX^{(1)}$	IND	L			210	440			
ISB1	Standby Current	$\overline{CE}_{L} = \overline{CE}_{R} = VH$	COM'L	L	45	115	40	105	35	95	mA
	(Both Ports - TTL Level Inputs)	$f = fMAX^{(1)}$	IND	L			40	120			
ISB2	Standby Current	<u>CE</u> "A" = V⊾ and CE"B" = V⊮ ⁽³⁾	COM'L	L	150	235	135	220	120	205	mA
	(One Port - TTL Level Inputs)	CE"B" = VIH ⁽⁵⁾ Active Port Outputs Disabled, f=fMAX ⁽¹⁾	IND	L			135	235			
ISB3	Full Standby Current	Both Ports CER and \overline{CE} L > VCC - 0.2V	COM'L	L	0.5	3.0	0.5	3.0	0.5	3.0	mA
	(Both Ports - CMOS Level Inputs)	$V \equiv V = 0.2V$ $V \equiv V = 0.2V$ or $V \equiv 0.2V$, $f = 0^{(2)}$	IND	L			0.5	3.0			
ISB4	Full Standby Current	\overline{CE} "A" $\leq 0.2V$ and	COM'L	L	160	210	130	190	110	170	mA
	(One Port - CMOS Level Inputs)	$\begin{array}{l} \overline{C}\overline{E}"B" \geq VCC \ - \ 0.2 V^{(5)} \\ \overline{V} N \geq VCC \ - \ 0.2 V \ or \\ \overline{V} N \leq \ 0.2 V, \ Active \ Port \\ \overline{Outputs \ Disabled}, \ f = \ fMAX^{(1)} \end{array}$	IND	L			130	205			

5653 tbl 09

NOTES:

1. At f = fMAX, address and control lines (except Output Enable) are cycling at the maximum frequency clock cycle of 1/tcvc, using "AC TEST CONDITIONS" at input levels of GND to 3V.

2. f = 0 means no address, clock, or control lines change. Applies only to input at CMOS level standby.

3. Port "A" may be either left or right port. Port "B" is the opposite from port "A".

4. Vcc = 5V, TA = 25° C for Typ, and are not production tested. Icc Dc(f=0) = 150mA (Typ).

5. CEx = VIL means $\overline{CE}_{0X} = VIL$ and $CE_{1X} = VIH$

CEx = VIH means $\overline{CE}_{0X} = VIH$ or $CE_{1X} = VIL$

CEx \leq 0.2V means $\overline{CE}_{0x} \leq 0.2V$ and CE1x \geq Vcc - 0.2V

 $CEx \geq Vcc$ - 0.2V means $\overline{CE} ox \geq Vcc$ - 0.2V or $CE1x \leq 0.2V$

"X" represents "L" for left port or "R" for right port.



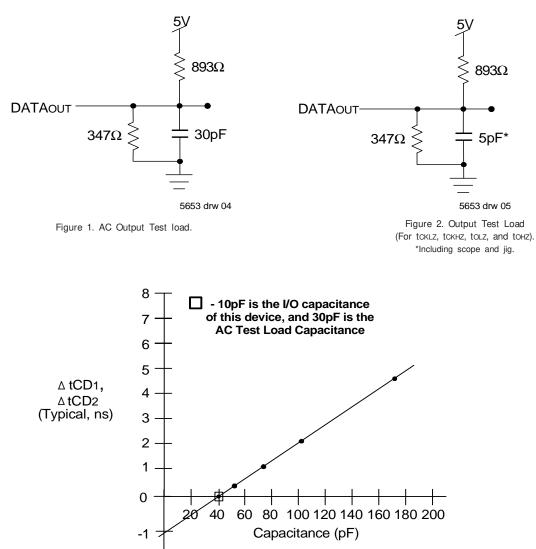
High-Speed 16/8K x 9 Synchronous Pipelined Dual-Port Static BAM

Industrial and Commercial Temperature Ranges

AC Test Conditions

Input Pulse Levels	GND to 3.0V
Input Rise/Fall Times	2ns Max.
Input Timing Reference Levels	1.5V
Output Reference Levels	1.5V
Output Load	Figures 1, 2 and 3

5653 tbl 10



5653 drw 06

Figure 3. Typical Output Derating (Lumped Capacitive Load).

High-Speed 16/8K x 9 Synchronous Pipelined Dual-Port Static RAM

AC Electrical Characteristics Over the Operating Temperature Range (Read and Write Cycle Timing)⁽³⁾ (Vcc = $5V \pm 10\%$, TA = $0^{\circ}C$ to $+70^{\circ}C$)

			69/59L6 'I Only		9/59L7 & Ind		69/59L9 I Only	
Symbol	Parameter	Min.	Max.	Min.	Max.	Min.	Max.	Unit
tCYC1	Clock Cycle Time (Flow-Through) ⁽²⁾	19	_	22	_	25	-	ns
tCYC2	Clock Cycle Time (Pipelined) ⁽²⁾	10	_	12	_	15	-	ns
tCH1	Clock High Time (Flow-Through) ⁽²⁾	6.5	_	7.5	_	12	-	ns
tCL1	Clock Low Time (Flow-Through) ⁽²⁾	6.5	_	7.5		12	_	ns
tCH2	Clock High Time (Pipelined) ⁽²⁾	4	_	5	_	6	-	ns
ta.2	Clock Low Time (Pipelined) ⁽²⁾	4		5		6	_	ns
tR	Clock Rise Time		3		3		3	ns
tF	Clock Fall Time		3		3		3	ns
tSA	Address Setup Time	3.5	_	4	_	4	-	ns
tHA	Address Hold Time	0		0		1		ns
tsc	Chip Enable Setup Time	3.5	_	4	_	4	-	ns
tHC	Chip Enable Hold Time	0		0		1		ns
tsв	Byte Enable Setup Time	3.5	_	4	_	4	-	ns
tнв	Byte Enable Hold Time	0		0		1		ns
tsw	R/W Setup Time	3.5		4		4		ns
t∺w	R/W Hold Time	0	_	0		1	_	ns
tsp	Input Data Setup Time	3.5	_	4		4	_	ns
tHD	Input Data Hold Time	0	_	0		1	_	ns
tSAD	ADS Setup Time	3.5		4		4	_	ns
thad	ADS Hold Time	0		0		1	_	ns
tSCN	CNTEN Setup Time	3.5		4		4		ns
tHCN	CNTEN Hold Time	0		0		1		ns
tSRST	CNTRST Setup Time	3.5		4		4		ns
tHRST	CNTRST Hold Time	0		0		1		ns
tOE	Output Enable to Data Valid		6.5		7.5		9	ns
toLz	Output Enable to Output Low-Z ⁽¹⁾	2		2		2		ns
tонz	Output Enable to Output High-Z ⁽¹⁾	1	7	1	7	1	7	ns
tCD1	Clock to Data Valid (Flow-Through) ⁽²⁾		15		18		20	ns
tCD2	Clock to Data Valid (Pipelined) ⁽²⁾		6.5		7.5		9	ns
tDC	Data Output Hold After Clock High	2		2		2	-	ns
tскнz	Clock High to Output High-Z ⁽¹⁾	2	9	2	9	2	9	ns
tCKLZ	Clock High to Output Low-Z ⁽¹⁾	2		2		2		ns
Port-to-Port	Delay		-	-	-	-	-	-
tCWDD	Write Port Clock High to Read Data Delay		24		28		35	ns
toos	Clock-to-Clock Setup Time		9		10		15	ns

1. Transition is measured 0mV from Low or High-impedance voltage with the Output Test Load (Figure 2). This parameter is guaranteed by device characterization, but is not production tested.

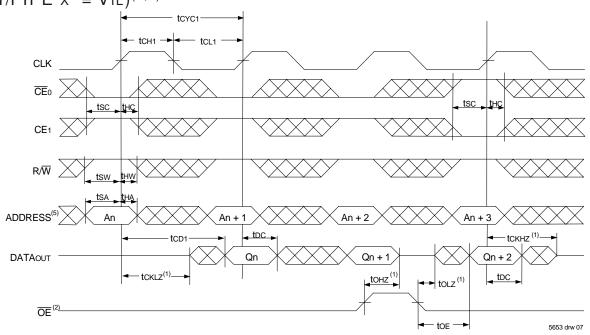
2. The Pipelined output parameters (tcvc2, tcD2) to either the Left or Right ports when FT/PIPE = VIH. Flow-Through parameters (tcvc1, tcD1) apply when FT/PIPE = VIL for that port.

3. All input signals are synchronous with respect to the clock except for the asynchronous Output Enable (\overline{OE}), \overline{FT} /PIPER and \overline{FT} /PIPEL

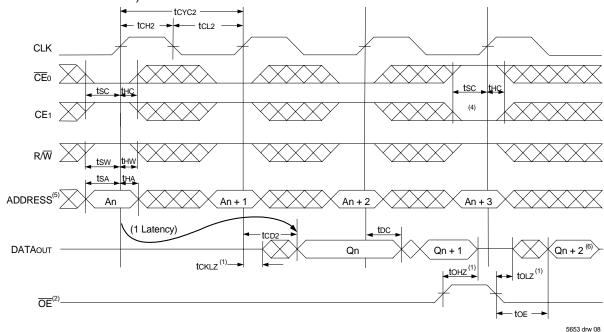
High-Speed 16/8K x 9 Synchronous Pinelined Dual-Port Static RAI

Industrial and Commercial Temperature Range

Timing Waveform of Read Cycle for Flow-Through Output $(\overline{FT}/PIPE^*X^* = VIL)^{(3,6)}$



Timing Waveform of Read Cycle for Pipelined Operation $(FT/PIPE"x" = VIH)^{(3,6)}$



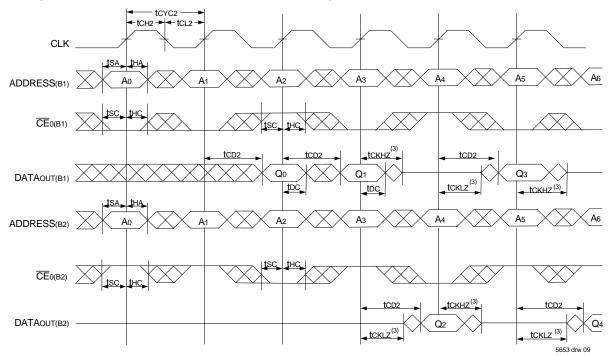
- 1. Transition is measured 0mV from Low or High-impedance voltage with the Output Test Load (Figure 2).
- 2. $\overline{\text{OE}}$ is asynchronously controlled; all other inputs are synchronous to the rising clock edge.
- 3. $\overline{ADS} = V_{IL}, \overline{CNTEN} \text{ and } \overline{CNTRST} = V_{IH}.$
- 4. The output is disabled (High-Impedance state) by CE0 = VIH or CE1 = VIL following the next rising edge of the clock. Refer to Truth Table 1.
- 5. Addresses do not have to be accessed sequentially since ADS = VIL constantly loads the address on the rising edge of the CLK; numbers
- are for reference use only. 6. "X" here denotes Left or Right port. The diagram is with respect to that port.



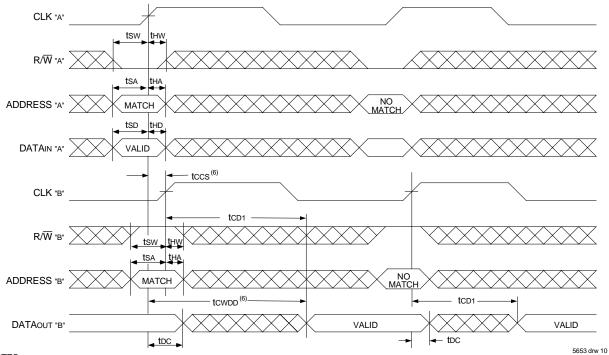
High-Speed 16/8K x 9 Synchronous Pipelined Dual-Port Static BA

Industrial and Commercial Temperature Rang

Timing Waveform of a Bank Select Pipelined Read^(1,2)



Timing Waveform of Write with Port-to-Port Flow-Through Read^(4,5,7)

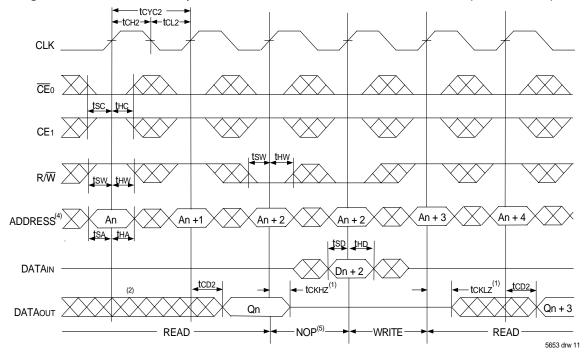


- 1. B1 Represents Bank #1; B2 Represents Bank #2. Each Bank consists of one IDT709169/59 for this waveform, and are setup for depth expansion in this example. ADDRESS(B1) = ADDRESS(B2) in this situation.
- 2. \overline{OE} and \overline{ADS} = VIL; CE1(B1), CE1(B2), R/W, \overline{CNTEN} , and \overline{CNTRST} = VIH.
- 3. Transition is measured 0mV from Low or High-impedance voltage with the Output Test Load (Figure 2).
- 4. \overline{CE}_0 and $\overline{ADS} = VIL$; CE1, \overline{CNTEN} , and $\overline{CNTRST} = VIH$.
- 5. $\overline{OE} = V_{IL}$ for the Right Port, which is being read from. $\overline{OE} = V_{IH}$ for the Left Port, which is being written to.
- If tccs ≤ maximum specified, then data from right port READ is not valid until the maximum specified for tcwpp.
 If tccs > maximum specified, then data from right port READ is not valid until tccs + tcp1. tcwpp does not apply in this case.
- 7. All timing is the same for both Left and Right ports. Port "A" may be either Left or Right port. Port "B" is the opposite from Port "A".

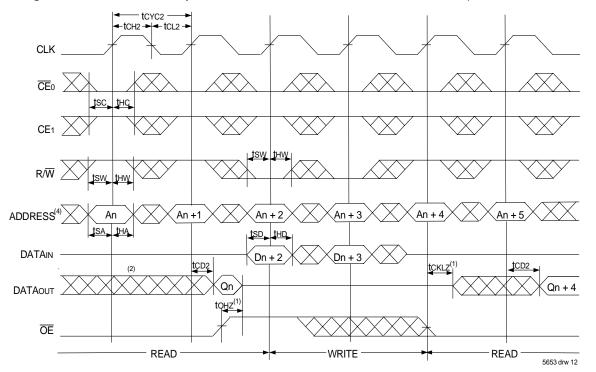


High-Speed 16/8K x 9 Synchronous Pipelined Dual-Port Static BAM

Timing Waveform of Pipelined Read-to-Write-to-Read ($\overline{OE} = VIL$)⁽³⁾



Timing Waveform of Pipelined Read-to-Write-to-Read (**OE** Controlled)⁽³⁾



NOTES:

1. Transition is measured 0mV from Low or High-impedance voltage with the Output Test Load (Figure 2).

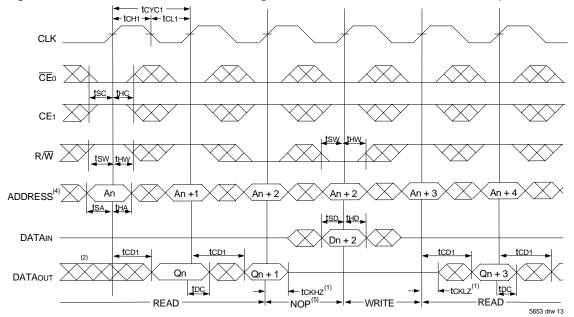
- 2. Output state (High, Low, or High-impedance) is determined by the previous cycle control signals.
- 3. \overline{CE}_0 and $\overline{ADS} = V_{IL}$; CE1, \overline{CNTEN} , and $\overline{CNTRST} = V_{IH}$. "NOP" is "No Operation".
- 4. Addresses do not have to be accessed sequentially since \overline{ADS} = ViL constantly loads the address on the rising edge of the CLK; numbers are for reference use only.
- 5. "NOP" is "No Operation." Data in memory at the selected address may be corrupted and should be re-written to guarantee data integrity.



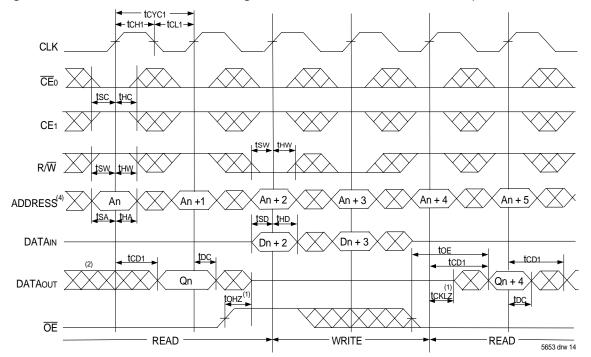
High-Speed 16/8K x 9 Synchronous Pipelined Dual-Port Static BAN

Industrial and Commercial Temperature Ran

Timing Waveform of Flow-Through Read-to-Write-to-Read ($\overline{OE} = VIL$)⁽³⁾



Timing Waveform of Flow -Through Read-to-Write-to-Read (**OE** Controlled)⁽³⁾

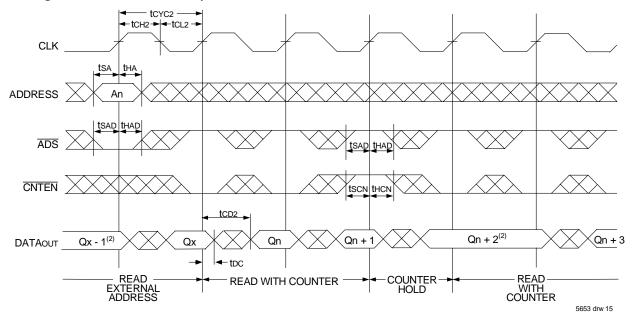


- 1. Transition is measured 0mV from Low or High-impedance voltage with the Output Test Load (Figure 2).
- 2. Output state (High, Low, or High-impedance is determined by the previous cycle control signals.
- 3. \overline{CE}_0 and $\overline{ADS} = V_{IL}$; CE1, \overline{CNTEN} , and $\overline{CNTRST} = V_{IH}$. "NOP" is "No Operation".
- 4. Addresses do not have to be accessed sequentially since ADS = VIL constantly loads the address on the rising edge of the CLK; numbers are for reference use only.
- 5. "NOP" is "No Operation." Data in memory at the selected address may be corrupted and should be re-written to guarantee data integrity.

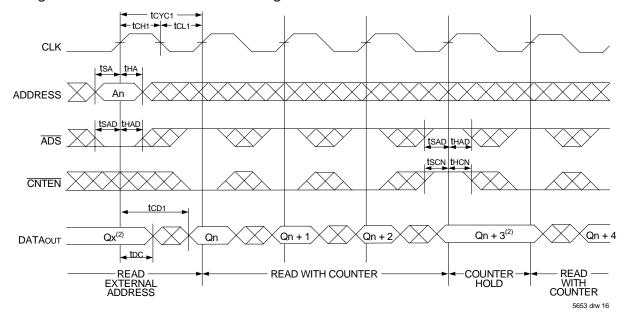


High-Speed 16/8K x 9 Synchronous Pipelined Dual-Port Static RAM

Timing Waveform of Pipelined Read with Address Counter Advance⁽¹⁾



Timing Waveform of Flow - Through Read with Address Counter Advance⁽¹⁾



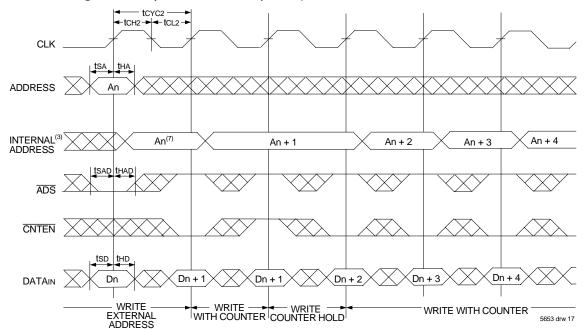
NOTES:

1. \overline{CE}_0 and \overline{OE} = VIL, CE1, R/ \overline{W} , and \overline{CNTRST} = VIH.

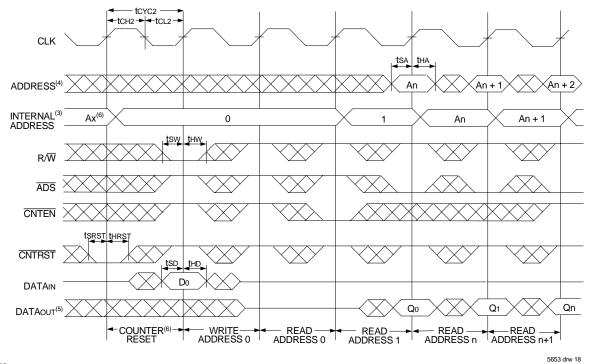
2. If there is no address change via \overline{ADS} = VIL (loading a new address) or \overline{CNTEN} = VIL (advancing the address), i.e. \overline{ADS} = VIH and \overline{CNTEN} = VIH, then the data output remains constant for subsequent clocks.



Timing Waveform of Write with Address Counter Advance (Flow -Through or Pipelined Outputs)⁽¹⁾



Timing Waveform of Counter Reset (Pipelined Outputs)⁽²⁾



- NOTES: 1. $\overrightarrow{CE_0}$ and $\overrightarrow{R/W} = V_{IL}$; CE_1 and $\overrightarrow{CNTRST} = V_{IH}$.
- 2. $\overline{CE}_0 = VIL; CE_1 = VIH.$
- 3. The "Internal Address" is equal to the "External Address" when $\overline{ADS} = VIL$ and equals the counter output when $\overline{ADS} = VIH$.
- 4. Addresses do not have to be accessed sequentially since $\overline{ADS} = VIL$ constantly loads the address on the rising edge of the CLK; numbers are for reference use only. 5. Output state (High, Low, or High-impedance) is determined by the previous cycle control signals.
- 6. No dead cycle exists during counter reset. A READ or WRITE cycle may be coincidental with the counter reset cycle.
- CNTEN = VIL advances Internal Address from 'An' to 'An +1'. The transition shown indicates the time required for the counter to advance. The 'An +1' Address is written 7. to during this cycle.

High-Speed 16/8K x 9 Synchronous Pipelined Dual-Port Static RAM

A Functional Description

The IDT709169/59 provides a true synchronous Dual-Port Static RAM interface. Registered inputs provide minimal set-up and hold times on address, data, and all critical control inputs. All internal registers are clocked on the rising edge of the clock signal, however, the self-timed internal write pulse is independent of the LOW to HIGH transition of the clock signal.

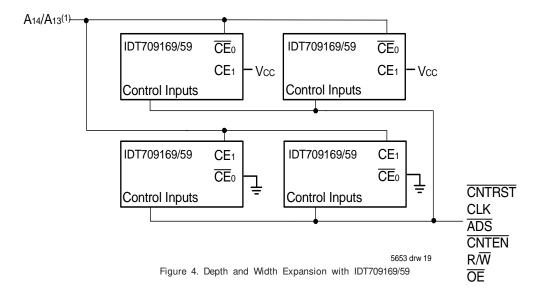
An asynchronous output enable is provided to ease asynchronous bus interfacing. Counter enable inputs are also provided to stall the operation of the address counters for fast interleaved memory applications.

 $\overline{CE}_0 = V_{IH}$ or $CE_1 = V_{IL}$ for one clock cycle will power down the internal circuitry to reduce static power consumption. Multiple chip enables allow easier banking of multiple IDT709169/59's for depth expansion configurations. When the Pipelined output mode is enabled, two cycles are required to get valid data on the outputs.

Depth and Width Expansion

The IDT709169/59 features dual chip enables (refer to Truth Table I) in order to facilitate rapid and simple depth expansion with no requirements for external logic. Figure 4 illustrates how to control the various chip enables in order to expand two devices in depth.

The IDT709169/59 can also be used in applications requiring expanded width, as indicated in Figure 4. Since the banks are allocated at the discretion of the user, the external controller can be set up to drive the input signals for the various devices as required to allow for 18-bit or wider applications.



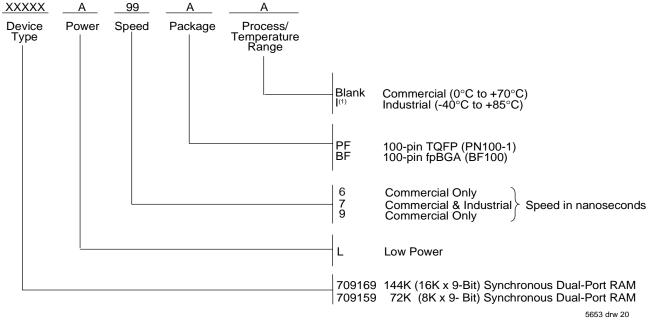
NOTE:

1. A14 is for IDT709169, A13 is for IDT709159.

High-Speed 16/8K x 9 Synchronous Pipelined Dual-Port Static RAM

Industrial and Commercial Temperature Ranges

Ordering Information



NOTE:

1. Contact your local sales office for Industrial temp range for other speeds, packages and powers. LEAD FINISH (SnPb) parts are in EOL process. Product Discontinuation Notice - PDN# SP-17-02

IDT Clock Solution for IDT709169/59 Dual-Port

	Dual-Port I/O	Specitications	Clock Specifications				IDT	IDT	
IDT Dual-Port Part Number	Voltage	I/O	Input Capacitance	Input Duty Cycle Requirement Maximum Frequency Tolerance			IDT Non-PLL Clock Device		
709169/59	5	TTL	9pF	40%	100	150ps	FCT88915TT	49FCT805T 49FCT806T 74FCT807T	

Datasheet Document History

- 07/08/02: Initial Public Release
- 08/18/03: Removed Preliminary status Page 16 Added IDT Clock Solution Table
- 01/29/09: Page 16 Removed "IDT" from orderable part number
- 02/05/14: 709169 Changed to Obsolete Status
- Product Discontinuation Notice PDN# F-09-01
- 04/26/19: Datasheet changed to Obsolete Status Product Discontinuation Notice - PDN# SP-17-02 Last time buy expires June 15, 2018

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